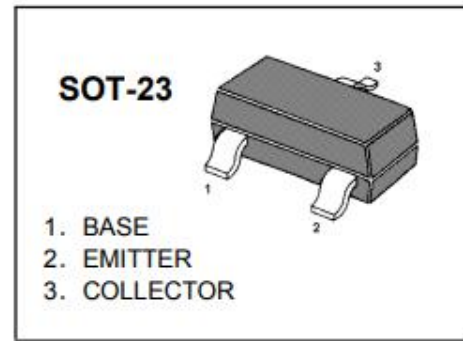
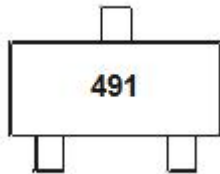


NPN Silicon Epitaxial Planar Transistor

Marking Information;



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Base Current	I_B	200	mA

Thermal Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	500	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	250	$^\circ\text{C} / \text{W}$
Thermal Resistance, Junction to Lead (Note 6)	$R_{\theta JL}$	197	$^\circ\text{C} / \text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

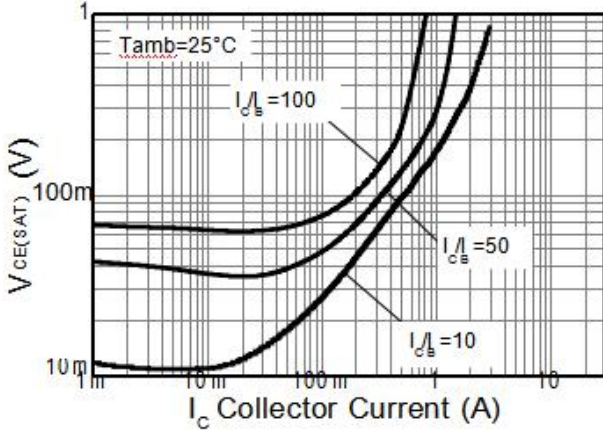


Characteristics at T_a = 25°C

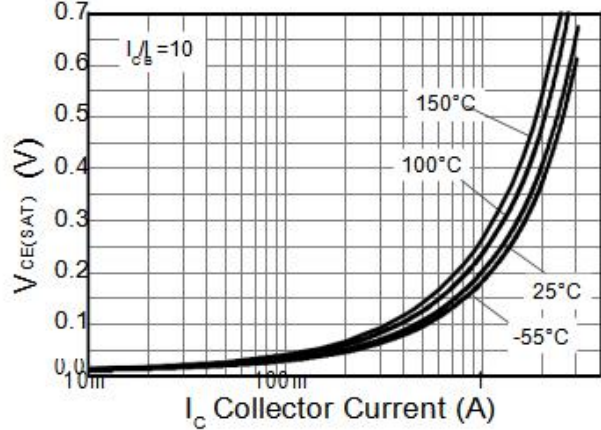
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	—	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	—	<1	100	nA	V _{CB} = 60V
Emitter Cutoff Current	I _{EBO}	—	<1	100	nA	V _{EB} = 5.6V
Collector Emitter Cutoff Current	I _{CES}	—	<1	100	nA	V _{CE} = 60V, V _{CES} = 60V
Static Forward Current Transfer Ratio (Note 8)	h _{FE}	100	140	—	—	I _C = 1mA, V _{CE} = 5V
		100	150	300		I _C = 500mA, V _{CE} = 5V
		80	120	—		I _C = 1A, V _{CE} = 5V
		30	40	—		I _C = 2A, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	—	100	150	mV	I _C = 500mA, I _B = 50mA
		—	160	250		I _C = 1A, I _B = 100mA
Base-Emitter Turn-On Voltage(Note 8)	V _{BE(on)}	—	830	1000	mV	I _C = 1A, V _{CE} = 5V
Base-Emitter Saturation Voltage(Note 8)	V _{BE(sat)}	—	965	1100	mV	I _C = 1A, I _B = 100mA
Output Capacitance	C _{obo}	—	—	10	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	150	—	—	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz



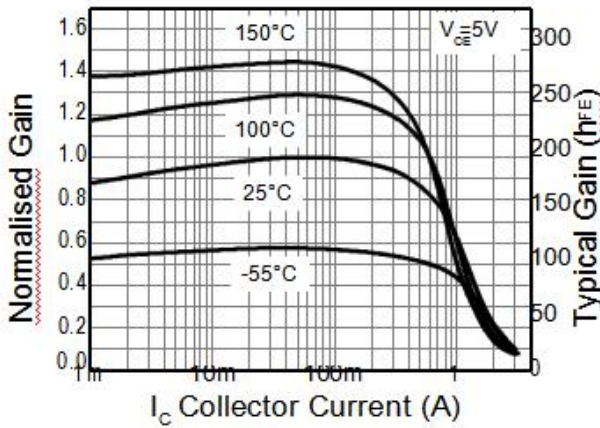
Typical Electrical Characteristics



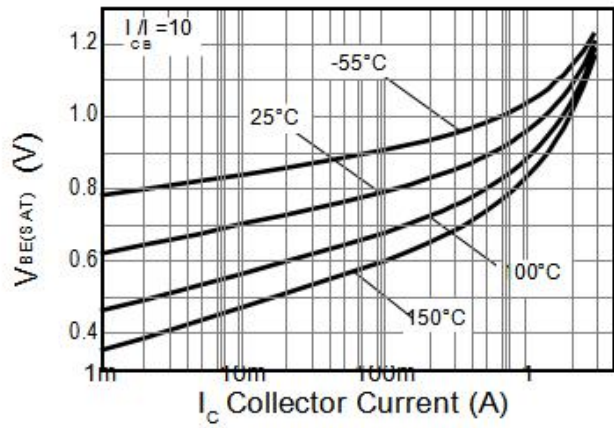
$V_{CE(SAT)} \ v \ I_C$



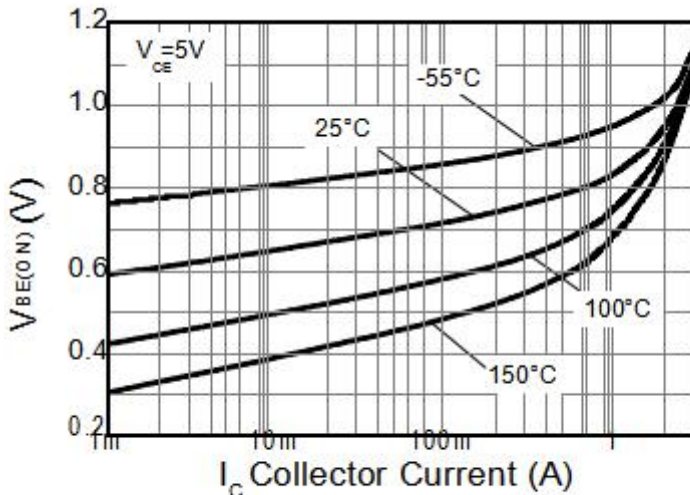
$V_{CE(SAT)} \ v \ I_C$



$h_{FE} \ v \ I_C$



$V_{BE(SAT)} \ v \ I_C$



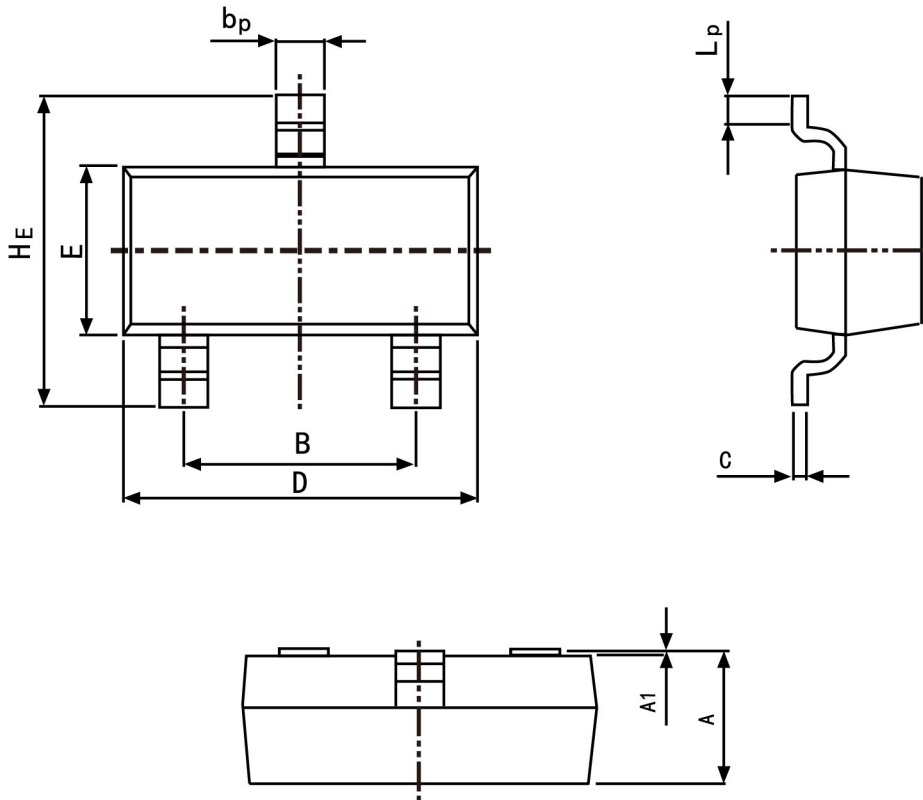
$V_{BE(ON)} \ v \ I_C$



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
bp	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
A1	0.100	0.013
Lp	0.20	0.50